Supporting Information

Luminescence Mechanism in hydrogenated Silicon Quantum Dots with Single Oxygen Ligand

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Figure S1. Structure of Si-QDs with different diameter and different passivation configurations.



Figure S2. HOMO, LUMO, HOMO-1, and LUMO+1 real space distribution of m-D+E Si-QDs.



Figure S3. Emission spectrum from first singlet excited to ground state for various smaller Si-QDs with more than one oxygen atoms. (a) double bonded, (b) epoxide ring bonded



Figure S4. Electron and hole distribution of Si-QDs with more than one oxygen atoms, in which cyan regions represent electron distribution and mag regions represent hole distribution. (a) 1.1-D- O_1 , (b) 1.1-D- O_2 , (c) 1.1-D- O_6 , (d) 1.3-D- O_1 , (e) 1.3-D- O_2 , (f) 1.3-D- O_3 , (g) 1.3-D- O_6 , (h) 1.3-D- O_8 , (i) 1.1-E- O_1 , (j) 1.1-E- O_2 , (k)1.1-E- O_6 , (l)1.3-E- O_1 , (m)1.3-E- O_6 , (n)1.3-E- O_8